[17p-PB3-1~48]Poster

10.1 Creation of new materials
10.2 Spin torque, spin current, circuits, and measurement technologies
10.3 Giant magnetoresistance (GMR), tunnel magnetoresistance (TMR) and magnetic recording technologies
10.4 Semiconductors, organic, optical, and quantum spintronics

Wed. Sep 17, 2014 4:00 PM - 6:00 PM  PB3 (Gymnasium2)

4:00 PM - 6:00 PM

[17p-PB3-26] Improvement of the spin-Seebeck voltage by annealing effect

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